Sheet 1 of 1

FORM PTO-1449

*EXAMINER:

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO. SEI PKHF-05004US 10

01/28/2009

SERIAL NO. 10/589 & E

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

Noboru ICHINOSE

FILING DATE

APPLICANT

November 27, 2006

SEP 1 8 2008

U.S. PATENT DOCUMENTS									
EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	3	FILI DA	
/D.W./	AA	6,897,560	05/24/2005	ОТА					
/D.W./	AB	7,319,249	01/15/2008	ICHINOSE					
/D.W./	AC	6,977,397	12/20/2005	ICHINOSE					
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	AF					000000000000000000000000000000000000000	900000 0000500K	72200000000000000000000000000000000000	988000000000000000000000000000000000000
FOREIGN PATENT DOCUMENTS									
		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB- CLASS	TRA YES	NSLA NO 1	<u>TION</u> PART.
/D.W./	AG	2002-093243		JAPAN (See U.S. 6,897,560)					A85
/D.W./	АН	2004-056098	02/15/2004	JAPAN (See U.S. 7,319,249 and U.S. 6,977,397)					A65
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	AJ			xxxxxxxxxxxxxxxxxxxxxxxxxxxxxxxxxxxxxx	2944800000000000000000000000000000000000	000000000000000000000000000000000000000	655000000055000	000000000000000000000000000000000000000	
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)									
/D.W./	AK	Harwig et al., "Electrical Properties of b-Ga2O3 Single Crystals. II," Journal of Solid State Chemistry Vol. 23, pages 205-211, 15 January 1978. (Previously Submitted)							
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XXXXX	AN	Frank J. et al., "electrical Doping of Gas-Sensitive, Semiconducting Ga2O3 Thin Films", In: Sensors and Actuators B: Chemical, August 1996, Vol. 34, pages 373 to 377. (Previously Submitted)							
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V	AP	Japanese Office Action dated August 5, 2008 with Partial English Translation							
EXAMINER	/1	Daniel Whalen/		DATE CONSIDERED	24 /00/000	0			

Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not

in conformance and not considered. Include copy of this form with next communication to applicant.